

## Bi-directional ESD Protection Diode in DFN1006-2L Package

**SE07N6S01GY**

### Features

- ◆ Working voltage: 7V
- ◆ Low capacitance: 15pF (Typical)
- ◆ Low leakage current: 0.1 $\mu$ A @  $V_{RWM}$
- ◆ Low clamping voltage
- ◆ Response Time is < 1 ns
- ◆ Meets MSL level 1

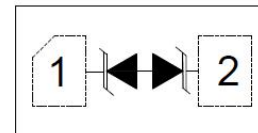
**DFN1006-2L**



### Applications

- ◆ Cellular handsets
- ◆ USB  $V_{BUS}$  and CC line protection
- ◆ Microphone line protection
- ◆ GPIO protection

### Pin Configuration



### Mechanical Characteristics

- ◆ DFN1006-2L package
- ◆ Molding Compound Flammability Rating: UL 94V-0
- ◆ Quantity Per Reel: 10,000pcs
- ◆ Reel Size: 7inch
- ◆ Lead Finish: Lead Free

### Protection Solution to Meet

- ◆ IEC61000-4-2 (ESD)  $\pm 30$ kV (air),  $\pm 30$ kV (contact)
- ◆ IEC61000-4-4 (EFT) 40A (5/50ns)
- ◆ IEC61000-4-5 (Lightning) 6A (8/20 $\mu$ s)

### Absolute Maximum Rating

Symbol	Parameter	Value	Units
$V_{ESD}$	ESD per IEC 61000-4-2 (Air)	$\pm 30$	KV
	ESD per IEC 61000-4-2 (Contact)	$\pm 30$	
$T_J$	Operating Temperature	-55 to +125	$^{\circ}$ C
$T_{STG}$	Storage Temperature	-55 to +150	$^{\circ}$ C
$T_{LST}$	Lead Soldering Temperature	260 (10 sec.)	$^{\circ}$ C

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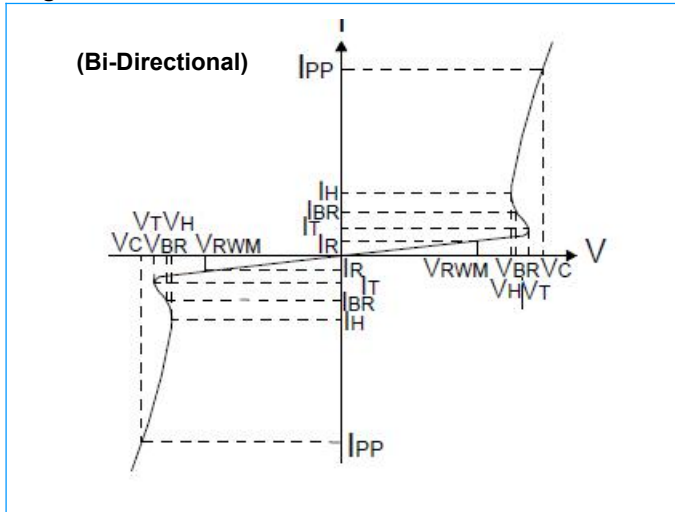
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Electrical Characteristics (@T<sub>A</sub>=25°C, unless otherwise specified)

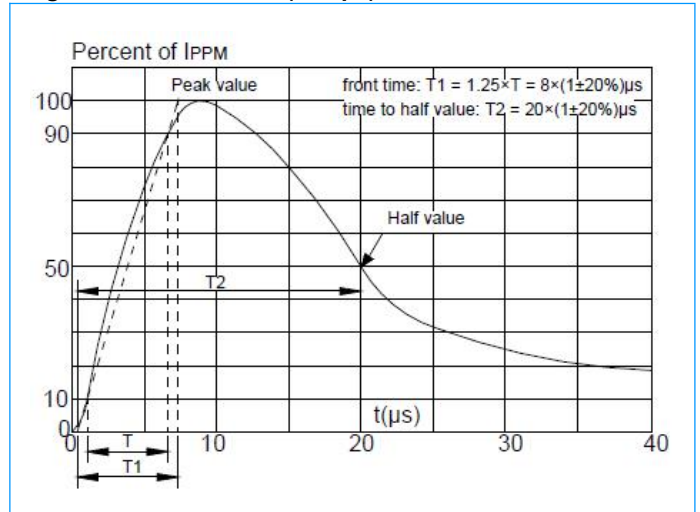
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Reverse Working Voltage	V <sub>RWM</sub>	--	--	--	7	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1mA	--	--	0.1	μA
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = ±7V, T=25°C	7.6	--	9	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 1A, t <sub>p</sub> = 8/20μs	--	9	--	V
		I <sub>PP</sub> = 6.5A, t <sub>p</sub> = 8/20μs	--	11	--	V
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> = 0V, f = 1MHz	--	15	--	pF

### Characteristic Curves

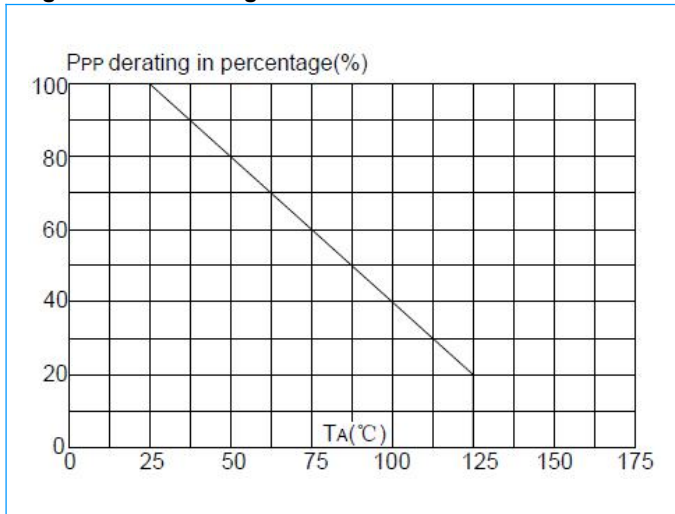
**Fig 1. V- I Curve Characteristics**



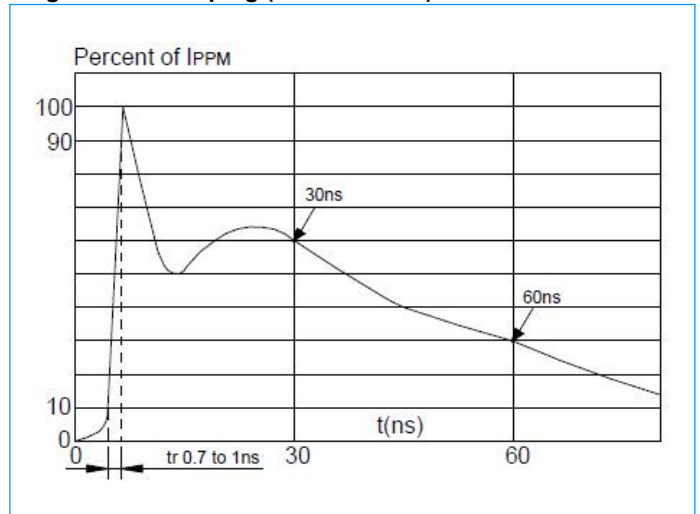
**Fig 2. Pulse Waveform (8/20μs)**



**Fig 3. Pulse Derating Curve**



**Fig 4. ESD Clamping (30kV Contact)**

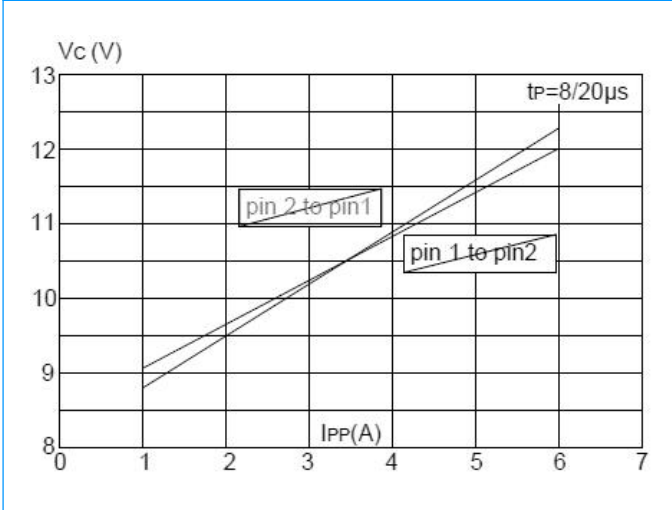


## Bi-directional ESD Protection Diode in DFN1006-2L Package

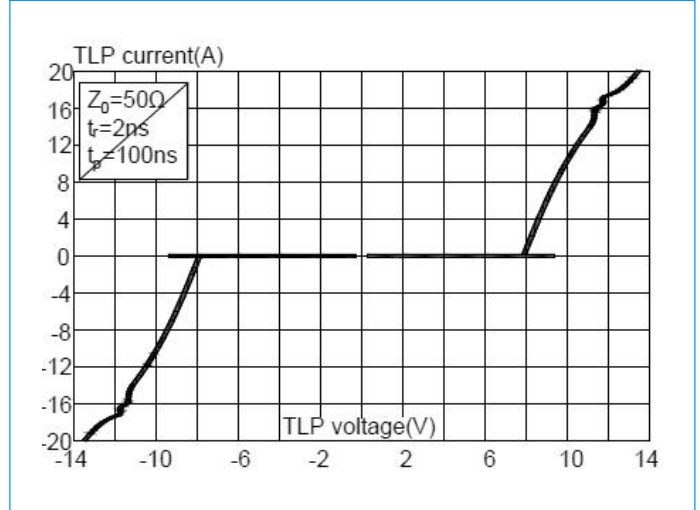
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### Characteristic Curves (Continue)

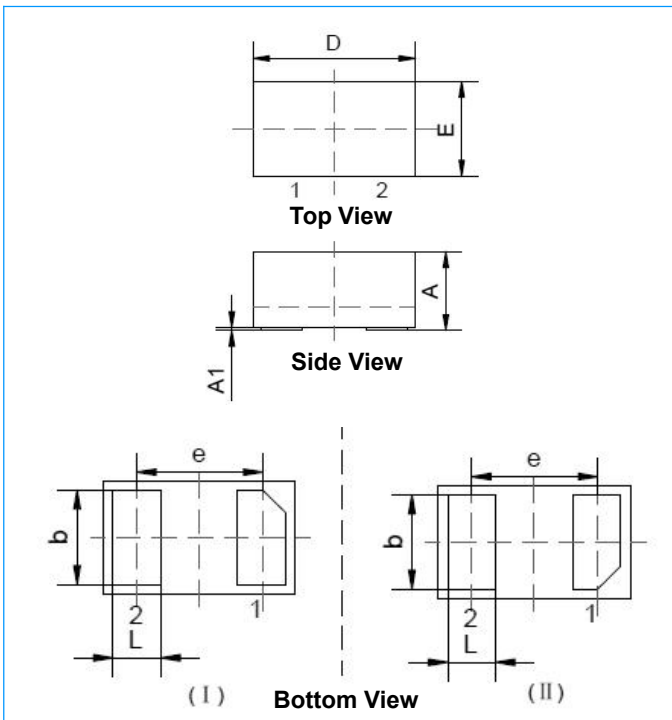
**Fig 5. Clamping Voltage vs. Peak Pulse Current**



**Fig 6. TLP Measurement**



### DFN1006-2L Package Outline & Dimensions



Symbol	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
<b>A</b>	0.40	0.50	0.55	0.016	0.020	0.022
<b>A1</b>	0.00	0.02	0.05	0.000	0.001	0.002
<b>b</b>	0.45	0.50	0.55	0.018	0.020	0.022
<b>D</b>	0.95	1.00	1.05	0.037	0.039	0.041
<b>e</b>	0.65 BSC			0.026 BSC		
<b>E</b>	0.55	0.60	0.65	0.022	0.024	0.026
<b>L</b>	0.20	0.25	0.30	0.008	0.010	0.012

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